

- 📧 Drafts
- 📧 Pending
- 📧 Active
 - 📧 L1: (3)
 - 📧 L2: (9)
 - 📧 L3: (8)
 - 📧 L4: (1)
 - 📧 L5: (2)
 - 📧 L6: (2)
- 📧 Failed
- 📧 Saved
- 📧 Favorite
- 📧 Tagged
- 📧 UDC
- 📧 Queue
- 📧 Trash

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Deputy Director: DA

5 and contact.clm.

□ **Prüfung**

♥ Highlights plz bring the following

U	I	FT	P	Document ID	Issue Dat	Pages	Title	Current OR	Current XR	Retrieval	Inventor	#	C	I	J	
1				US 20030224611	20031204	60	Manufacturing method of	438/706			Seta, Shoji et al.					
2				US 20030082876	20030501	28	Vertical DRAM	438/243	257/302		Mandelman, Jack A.					
3				US 20030008469	20030109	28	punchthrough stop self- DRAM cell capacitor and	438/396	257/E21.01		et al.					
4				US 20020163842	20021107	7	manufacturing method th DRAM cell configuration	365/200	257/E21.01		Hwang, Yoo-Sang et					
5				US 20020102843	20020801	88	and method for fabricat Semiconductor device	438/672	257/E21.25		et al.					
6				US 20020066925	20020606	18	and manufacturing metho Structure and method	257/329	257/E21.65		Seta, Shoji et al.					
7				US 20020059899	20020523	60	for forming a body cont Manufacturing method of	117/97	117/84;		Gruening, Ulrike					
8				US 6660581	20031209	21	semiconductor devices b Method of forming	438/242	257/E21.25		et al.					
9				B1 6642566	20031104	15	single bitline contact Asymmetric inside	438/243;	438/270		Seta, Shoji et al.					
10				B1 6605542	20030812	56	spacer for vertical tra Manufacturing method of	257/302	257/301		Yang, Haining et					
11				B2 6593612	20030715	17	semiconductor devices b Structure and method	438/700	257/E21.25		al.					
12				B2 6479343	20021112	27	for forming a body cont DRAM cell capacitor and	257/301	257/302;		Mandelman, Jack A.					
13								257/E21.65	257/E21.01		et al.					
14											Hwang, Yoo-Sang et					

(10) 29 and 11 (trench or cavity) same (wall or sidewall)

9 and ((spacer\$1 or sidewall\$1 or (side adj wall)) near (mask or etch\$3))

☒ Highlight all hit terms initially.

 BRIEF form
  IS&R form
  Image
  Text
  HTML

U	1	PT	P	Document ID	Issue	Date	Pages	Title	Current OR	Current XRef	R	Inventor	S	C
1	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030169629 A1	20030911	49		Semiconductor memory cell configuration and a method for producing the configuration	365/200	257/E21.652	<input type="checkbox"/>	Goebel, Bernd et al.	<input type="checkbox"/>	<input type="checkbox"/>
2	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020185469 A1	20021212	44		Method of micromachining a multi-part cavity	216/41	257/E21.218; 257/E21.235	<input type="checkbox"/>	Podlesnik, Dragan et al.	<input type="checkbox"/>	<input type="checkbox"/>
3	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020163842 A1	20021107	7		Dram cell configuration and method for fabricating the dram cell configuration	365/200		<input type="checkbox"/>	Benzinger, Herbert et al.	<input type="checkbox"/>	<input type="checkbox"/>
4	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020066925 A1	20020606	18		Structure and method for forming a body contact for vertical transistor cells	257/329	257/E21.653; 438/212	<input type="checkbox"/>	Gruening, Ulrike et al.	<input type="checkbox"/>	<input type="checkbox"/>
5	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6548850 B1	20030415	18		Trench capacitor configuration and method of producing it	257/301	257/296; 257/E21.653	<input type="checkbox"/>	Gernhard, Stefan et al.	<input type="checkbox"/>	<input type="checkbox"/>
6	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6451648 B1	20020917	11		Process for buried-strap self-aligned to deep storage trench	438/243	257/E21.651; 438/248; 438/386;	<input type="checkbox"/>	Gruening, Ulrike et al.	<input type="checkbox"/>	<input type="checkbox"/>
7	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6426526 B1	20020730	23		Single sided buried strap	257/302	257/301; 257/E21.652	<input type="checkbox"/>	Divakaruni, Ramachandra et al.	<input type="checkbox"/>	<input type="checkbox"/>
8	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6426253 B1	20020730	19		Method of forming a vertically oriented device in an integrated circuit	438/243	257/E21.551; 257/E21.629; 257/E21.653;	<input type="checkbox"/>	Tews, Helmut Horst et al.	<input type="checkbox"/>	<input type="checkbox"/>
9	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6063658	20000516	21		Methods of making a trench	438/248	257/E21.652; 257/E21.653;	<input type="checkbox"/>	Horak, David	<input type="checkbox"/>	<input type="checkbox"/>

Bandy

NAME